

K L Wang

List of Publications by Year in descending order

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6078
citing authors

#	ARTICLE	IF	CITATIONS
1	Tunable Magnetoelastic Effects in Voltage-Controlled Exchange-Coupled Composite Multiferroic Microstructures. ACS Applied Materials & Interfaces, 2020, 12, 6752-6760.	4.0	12
2	Field-Free Switching of Perpendicular Magnetization through Voltage-Gated Spin-Orbit Torque. , 2019, , .		30
3	Effect of CoFe dusting layer and annealing on the magnetic properties of sputtered Ta/W/CoFeB/CoFe/MgO layer structures. Journal Physics D: Applied Physics, 2019, 53, .	1.3	0
4	Perpendicular magnetic tunnel junction with W seed and capping layers. Journal of Applied Physics, 2017, 121, .	1.1	21
5	Strain induced exchange-spring magnetic behavior in amorphous (TbDy)Fe ₂ thin films. Journal of Applied Physics, 2017, 121, 043911.	1.1	5
6	A Spintronic Voltage-Controlled Stochastic Oscillator for Event-Driven Random Sampling. IEEE Electron Device Letters, 2017, 38, 281-284.	2.2	15
7	Analog to Stochastic Bit Stream Converter Utilizing Voltage-Assisted Spin Hall Effect. IEEE Electron Device Letters, 2017, 38, 1343-1346.	2.2	16
8	Ultra-low switching energy and scaling in electric-field-controlled nanoscale magnetic tunnel junctions with high resistance-area product. Applied Physics Letters, 2016, 108, .	1.5	186
9	Electric-field-driven magnetization switching and nonlinear magnetoelasticity in Au/FeCo/MgO heterostructures. Scientific Reports, 2016, 6, 29815.	1.6	48
10	In-plane magnetic field effect on switching voltage and thermal stability in electric-field-controlled perpendicular magnetic tunnel junctions. AIP Advances, 2016, 6, 075014.	0.6	19
11	Insight into the antiferromagnetic structure manipulated by electronic reconstruction. Physical Review B, 2016, 94, .	1.1	16
12	Oscillatory magnetic anisotropy and spin-reorientation induced by heavy-metal cap in Cu/FeCo/ M () Tj ETQq0 0 0 rgBT /Overlock 10 Tf 5	1.1	6
13	Giant voltage modulation of magnetic anisotropy in strained heavy metal/magnet/insulator heterostructures. Physical Review B, 2015, 92, .	1.1	79
14	Electric manipulation of skyrmions in metals and insulators. , 2015, , .		0
15	Characterization of Trapped Charge in Ge/LixGe Core/Shell Structure during Lithiation using Off-axis Electron Holography. Microscopy and Microanalysis, 2015, 21, 1397-1398.	0.2	0
16	Impact of microstrip width and annealing time on the characteristics of micro-scale graphene FETs. , 2014, , .		0
17	Electric field control and effect of Pd capping on magnetocrystalline anisotropy in FePd thin films: A first-principles study. Physical Review B, 2014, 89, .	1.1	41
18	Influence of substrate type and quality on carrier mobility in graphene nanoribbons. Journal of Applied Physics, 2013, 114, .	1.1	20

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19	Electric-field-induced thermally assisted switching of monodomain magnetic bits. Journal of Applied Physics, 2013, 113, .	1.1	27
20	Low-power non-volatile spintronic memory: STT-RAM and beyond. Journal Physics D: Applied Physics, 2013, 46, 074003.	1.3	391
21	High-quality Bi ₂ Te ₃ thin films grown on mica substrates for potential optoelectronic applications. Applied Physics Letters, 2013, 103, .	1.5	50
22	NONVOLATILE SPINTRONICS: PERSPECTIVES ON INSTANT-ON NONVOLATILE NANOELECTRONIC SYSTEMS. Spin, 2012, 02, 1250009.	0.6	28
23	Ultrafast spin torque memory based on magnetic tunnel junctions with combined in-plane and perpendicular polarizers. , 2012, , .		1
24	Magnetically doped semiconducting topological insulators. Journal of Applied Physics, 2012, 112, .	1.1	75
25	Reduction of switching current density in perpendicular magnetic tunnel junctions by tuning the anisotropy of the CoFeB free layer. Journal of Applied Physics, 2012, 111, 07C907.	1.1	28
26	Two dimensional crystal tunneling devices for THz operation. Applied Physics Letters, 2012, 101, .	1.5	27
27	Nanoscale magnetic tunnel junction sensors with perpendicular anisotropy sensing layer. Applied Physics Letters, 2012, 101, 062412.	1.5	48
28	Low writing energy and sub nanosecond spin torque transfer switching of in-plane magnetic tunnel junction for spin torque transfer random access memory. Journal of Applied Physics, 2011, 109, .	1.1	99
29	Switching current reduction using perpendicular anisotropy in CoFeB/MgO magnetic tunnel junctions. Applied Physics Letters, 2011, 98, .	1.5	169
30	Effect of resistance-area product on spin-transfer switching in MgO-based magnetic tunnel junction memory cells. Applied Physics Letters, 2011, 98, .	1.5	49
31	Epitaxial growth of high mobility Bi ₂ Se ₃ thin films on CdS. Applied Physics Letters, 2011, 98, 242102.	1.5	85
32	Deep subnanosecond spin torque switching in magnetic tunnel junctions with combined in-plane and perpendicular polarizers. Applied Physics Letters, 2011, 98, .	1.5	82
33	Enhancement of microwave emission in magnetic tunnel junction oscillators through in-plane field orientation. Applied Physics Letters, 2011, 99, .	1.5	39
34	Magnetic and Transport Properties of Mn-ion implanted Si. , 2010, , .		0
35	Fermi level depinning of Ge Schottky contacts using single crystalline MgO. , 2009, , .		0
36	Bias voltage dependence of magnetic tunnel junctions comprising amorphous ferromagnetic CoFeSiB layer with double barriers. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1847-1850.	0.8	0

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37	Cellular Nonlinear Network with Spin Wave Bus. , 2007, , .		0
38	Optical properties of Y2O3 thin films doped with spatially controlled Er3+ by atomic layer deposition. Journal of Applied Physics, 2007, 101, .	1.1	23
39	Nanoscale modules with full spin-wave interconnectivity. Journal of Experimental Nanoscience, 2007, 2, 73-86.	1.3	3
40	Nanostructure and temperature-dependent photoluminescence of Er-doped Y2O3 thin films for micro-optoelectronic integrated circuits. Journal of Applied Physics, 2006, 100, 073512.	1.1	27
41	Transport study of a single bismuth nanowire fabricated by the silver and silicon nanowire shadow masks. Applied Physics Letters, 2006, 89, 141503.	1.5	36
42	Sb surfactant-mediated SiGe graded layers for Ge photodiodes integrated on Si. Journal of Applied Physics, 2006, 99, 024504.	1.1	12
43	Microstructural and optical properties of self-organized GaN quantum-dot assemblies. Journal of Applied Physics, 2005, 97, 043527.	1.1	9
44	Characterization of nanostructure in Si1-xGex epilayers using x-ray reflectivity and fluorescence techniques. Journal of Applied Physics, 2005, 98, 074309.	1.1	5
45	L-valley electrons in SiGe heterostructures: highly anisotropic and tunable Zeeman and Rashba-like spin splittings. AIP Conference Proceedings, 2005, , .	0.3	0
46	Tunable normal incidence Ge quantum dot midinfrared detectors. Journal of Applied Physics, 2004, 96, 773-776.	1.1	20
47	Interwell exciton dispersion engineering, coherent phonons generation and optical detection of exciton condensate. Physica Status Solidi (B): Basic Research, 2004, 241, 85-100.	0.7	2
48	Quantum Computation by Electron Spin in SiGe Heterostructures. , 2004, , 465-476.		1
49	Temperature effect on the formation of uniform self-assembled Ge dots. Applied Physics Letters, 2003, 83, 2847-2849.	1.5	41
50	Observation of magnetic-field-enhanced source current of accumulated p-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2003, 82, 3547-3549.	1.5	2
51	Cross-plane thermal conductivity of self-assembled Ge quantum dot superlattices. Physical Review B, 2003, 67, .	1.1	43
52	Optical phonons in self-assembled Ge quantum dot superlattices: Strain relaxation effects. Journal of Applied Physics, 2002, 92, 6804-6808.	1.1	39
53	Measurements of anisotropic thermoelectric properties in superlattices. Applied Physics Letters, 2002, 81, 3588-3590.	1.5	137
54	Simultaneous measurements of Seebeck coefficient and thermal conductivity across superlattice. Applied Physics Letters, 2002, 80, 1758-1760.	1.5	117

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55	High-quality Ge films on Si substrates using Sb surfactant-mediated graded SiGe buffers. Applied Physics Letters, 2001, 79, 3431-3433.	1.5	39
56	Optical study of SiGe films grown with low temperature Si buffer. Materials Research Society Symposia Proceedings, 2001, 673, 1.	0.1	0
57	In-plane Thermal and Electronic Transport in Quantum Dot Superlattice. Materials Research Society Symposia Proceedings, 2001, 677, 491.	0.1	0
58	Photoluminescence of InAs quantum dots coupled to a two-dimensional electron gas. Journal of Electronic Materials, 2001, 30, 459-462.	1.0	1
59	Infrared multispectral detection using Si/SixGe1-x quantum well infrared photodetectors. Applied Physics Letters, 2001, 78, 495-497.	1.5	24
60	Modification of the three-phonon Umklapp process in a quantum wire. Applied Physics Letters, 2001, 79, 851-853.	1.5	21
61	Towards Si1-xGex quantum-well resonant-state terahertz laser. Applied Physics Letters, 2001, 79, 3909-3911.	1.5	60
62	Response to "Comment on "Optical and acoustic phonon modes in self-organized Ge quantum dot superlattices" [Appl. Phys. Lett. 78, 1160 (2001)]. Applied Physics Letters, 2001, 78, 1162-1163.	1.5	5
63	Effective compliant substrate for low-dislocation relaxed SiGe growth. Applied Physics Letters, 2001, 78, 1219-1221.	1.5	32
64	Spin-wave utilization in a quantum computer. Physical Review A, 2001, 64, .	1.0	27
65	Compliant effect of low-temperature Si buffer for SiGe growth. Applied Physics Letters, 2001, 78, 454-456.	1.5	40
66	High-quality strain-relaxed SiGe films grown with low temperature Si buffer. Journal of Applied Physics, 2001, 89, 8279-8283.	1.1	43
67	Study of phonons in self-organized multiple Ge quantum dots. Journal of Electronic Materials, 2000, 29, 554-556.	1.0	4
68	Investigation of flicker noise and deep-levels in GaN/AlGaN transistors. Journal of Electronic Materials, 2000, 29, 297-301.	1.0	33
69	Low-dislocation relaxed SiGe grown on an effective compliant substrate. Journal of Electronic Materials, 2000, 29, 950-955.	1.0	9
70	Regimented placement of self-assembled Ge dots on selectively grown Si mesas. Applied Physics Letters, 2000, 76, 3591-3593.	1.5	97
71	High-quality strain-relaxed SiGe alloy grown on implanted silicon "on" insulator substrate. Applied Physics Letters, 2000, 76, 2680-2682.	1.5	48
72	In-plane lattice thermal conductivity of a quantum-dot superlattice. Journal of Applied Physics, 2000, 88, 696-699.	1.1	94

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73	Experimental proof-of-principle investigation of enhanced Z3DT in (001) oriented Si/Ge superlattices. Applied Physics Letters, 2000, 77, 1490-1492.	1.5	169
74	Thermoelectric figure of merit enhancement in a quantum dot superlattice. Nanotechnology, 2000, 11, 327-331.	1.3	50
75	Changes in luminescence emission induced by proton irradiation: InGaAs/GaAs quantum wells and quantum dots. Applied Physics Letters, 2000, 76, 2074-2076.	1.5	106
76	Optical and acoustic phonon modes in self-organized Ge quantum dot superlattices. Applied Physics Letters, 2000, 76, 586-588.	1.5	54
77	Raman spectroscopy of electrochemically self-assembled CdS quantum dots. Applied Physics Letters, 2000, 76, 137-139.	1.5	136
78	Controlled arrangement of self-organized Ge islands on patterned Si (001) substrates. Applied Physics Letters, 1999, 75, 2752-2754.	1.5	144
79	Response to "Comment on "Raman scattering from a self-organized Ge dot superlattice" [Appl. Phys. Lett. 75, 3572 (1999)]. Applied Physics Letters, 1999, 75, 3574-3575.	1.5	13
80	Self-organized Ge quantum wires on Si(111) substrates. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1406-1409.	0.9	2
81	Effect of channel doping on the low-frequency noise in GaN/AlGaN heterostructure field-effect transistors. Applied Physics Letters, 1999, 75, 2064-2066.	1.5	35
82	Thermal relaxation processes probed by intersubband and inter-valence-band transitions in Si/Si $_{1-x}$ Ge $_x$ multiple quantum wells. Applied Physics Letters, 1999, 75, 2232-2234.	1.5	2
83	Raman scattering and infrared absorption in multiple boron-doped Ge dots. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1420-1424.	0.9	2
84	Observation of inter-sub-level transitions in modulation-doped Ge quantum dots. Applied Physics Letters, 1999, 75, 1745-1747.	1.5	32
85	Growth and study of self-organized Ge quantum wires on Si(111) substrates. Applied Physics Letters, 1999, 74, 2471-2473.	1.5	28
86	A surfactant-mediated relaxed Si $_{0.5}$ Ge $_{0.5}$ graded layer with a very low threading dislocation density and smooth surface. Applied Physics Letters, 1999, 75, 1586-1588.	1.5	68
87	Fabrication of nanometer size photoresist wire patterns with a silver nanocrystal shadowmask. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1425-1427.	0.9	11
88	Formation of nanometer-scale InAs islands on silicon. Journal of Electronic Materials, 1999, 28, 432-436.	1.0	14
89	Lateral Transport in Strained SiGe Quantum Wells Doped with Boron. Physica Status Solidi (B): Basic Research, 1999, 211, 495-499.	0.7	8
90	Intersubband absorption in boron-doped multiple Ge quantum dots. Applied Physics Letters, 1999, 74, 185-187.	1.5	93

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91	Tunnel diodes fabricated from CdSe nanocrystal monolayers. Applied Physics Letters, 1999, 74, 317-319.	1.5	46
92	Raman scattering from a self-organized Ge dot superlattice. Applied Physics Letters, 1999, 74, 1863-1865.	1.5	46
93	Temperature-dependent morphology of three-dimensional InAs islands grown on silicon. Applied Physics Letters, 1999, 75, 1273-1275.	1.5	15
94	Low frequency noise sources in AlGaIn/GaN HEMTs. , 1999, , .		0
95	Inter-Sub-Level Spectroscopy of P-Type Modulation-Doped Ge Quantum Dots. Materials Research Society Symposia Proceedings, 1999, 571, 15.	0.1	0
96	Mechanism of the Preferential Edge-Positioning of Self-Organized Ge Quantum Dots on Si Mesas. Materials Research Society Symposia Proceedings, 1999, 571, 31.	0.1	1
97	Demonstration of Si homojunction far-infrared detectors. Applied Physics Letters, 1998, 72, 2307-2309.	1.5	29
98	Correlation between barrier height and band offsets in metal/Si _{1-x} Ge _x /Si heterostructures. Applied Physics Letters, 1998, 73, 3920-3922.	1.5	10
99	Persistent photoconductivity in Si delta-doped GaAs at low doping concentration. Applied Physics Letters, 1998, 73, 3235-3237.	1.5	6
100	Localized-state band induced by B δ -doping in Si/Si _{1-x} Ge _x /Si quantum wells. Physical Review B, 1998, 57, 6579-6583.	1.1	9
101	Experimental Study of Phonon-Folding in Si/Ge and Si/SiGe Structures Designed for Thermoelectric Applications. Materials Research Society Symposia Proceedings, 1998, 545, 111.	0.1	3
102	Thermal Conductivity and Phonon Engineering in Low-Dimensional Structures. Materials Research Society Symposia Proceedings, 1998, 545, 357.	0.1	8
103	Experimental Study of the Effect of the Quantum Well Structures on the Thermoelectric Figure of Merit in Si/Si _{1-x} Ge _x System. Materials Research Society Symposia Proceedings, 1998, 545, 369.	0.1	9
104	Far-infrared free-hole absorption in epitaxial silicon films for homojunction detectors. Applied Physics Letters, 1997, 71, 515-517.	1.5	15
105	SiGe quantum dots prepared on an ordered mesoporous silica coated Si substrate. Applied Physics Letters, 1997, 71, 2448-2450.	1.5	36
106	A Si bistable diode utilizing interband tunneling junctions. Applied Physics Letters, 1997, 71, 2190-2192.	1.5	8
107	Lattice modification and luminescence of dry-etched Si-Si _{1-x} Ge _x quantum dots. , 1997, 3007, 170.		6
108	Observation of new type resonances in triple barrier resonant tunneling diodes. Journal of Applied Physics, 1997, 82, 2980-2983.	1.1	1

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109	Strain-conserving doping of a pseudomorphic metastable Ge _{0.06} Si _{0.94} layer on Si(100) by low-dose BF ₂ +implantation. Journal of Applied Physics, 1997, 81, 1695-1699.	1.1	9
110	Quantum Confinement Effects on the Thermoelectric Figure of Merit in Si/Si _{1-x} Ge _x System. Materials Research Society Symposia Proceedings, 1997, 478, 169.	0.1	2
111	Prospects for High Thermoelectric Figures of Merit in 2D Systems. Materials Research Society Symposia Proceedings, 1997, 478, 55.	0.1	13
112	Free Carrier Absorption in P-Type Epitaxial Si and GaAs Films for far-Infrared Detection. Materials Research Society Symposia Proceedings, 1997, 484, 199.	0.1	0
113	Control of Sizes and Optical Emission of Sige Quantum Dots Prepared on Ordered Mesoporous Silica Coated Si Wafer. Materials Research Society Symposia Proceedings, 1997, 486, 255.	0.1	2
114	Effect of doping density on capacitance of resonant tunneling diodes. Journal of Applied Physics, 1997, 82, 5206-5209.	1.1	2
115	Pressure and strain sensors based on intervalley electron transfer in AlGaAs. Applied Physics Letters, 1997, 70, 3437-3439.	1.5	2
116	Facet Formation in Submicron Selective Growth of Si/SiGe. Materials Research Society Symposia Proceedings, 1996, 448, 241.	0.1	1
117	Effect of Quantum-Well Structures on the Thermoelectric Figure of Merit in the Si/Si _{1-x} Ge _x System. Materials Research Society Symposia Proceedings, 1996, 452, 261.	0.1	6
118	Microstructure of Oxidized Ge _{0.78} Si _{0.12} annealed in a Reducing Ambient. Materials Research Society Symposia Proceedings, 1995, 379, 127.	0.1	0
119	Solid-Phase Epitaxial Regrowth and Dopant Activation of Arsenic. Implanted Metastable Pseudomorphic Ge _{0.08} Si _{0.92} AND Ge _{0.16} Si _{0.84} ON Si(100). Materials Research Society Symposia Proceedings, 1995, 379, 467.	0.1	0
120	SiGe band engineering for MOS, CMOS and quantum effect devices. Journal of Materials Science: Materials in Electronics, 1995, 6, 311-324.	1.1	40
121	Reduction of the dislocation density for GaAs thin films on Si substrates grown by molecular beam epitaxy using the two-step growth method. Journal of Materials Science Letters, 1995, 14, 1340-1343.	0.5	0
122	Chemical Etching of Si _{1-x} Ge _x in HF:H ₂ O:H ₂ O ₂ :CH ₃ COOH. J 1260-1266.	1.3	79
123	Interfacial roughness scaling and strain in lattice mismatched Si _{0.4} Ge _{0.6} thin films on Si. Applied Physics Letters, 1995, 67, 629-631.	1.5	15
124	Vertical transport in GaAs/AlxGa _{1-x} As superlattices by a microwave time-of-flight technique. Physical Review B, 1995, 51, 17614-17617.	1.1	4
125	Strain transfer between thin films on buried oxide and its application in heteroepitaxial crystal growth. Philosophical Magazine Letters, 1995, 72, 231-237.	0.5	10
126	GeSi/Si bistable diode exhibiting a large on/off conductance ratio. Applied Physics Letters, 1995, 66, 2403-2405.	1.5	6

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127	Normalâ€incidence strainedâ€layer superlattice Ge _{0.5} Si _{0.5} /Si photodiodes near 1.3 μ m. Applied Physics Letters, 1995, 67, 566-568.	1.5	58
128	Dependence of damage and strain on the temperature of Si irradiation in epitaxial Ge _{0.10} Si _{0.90} films on Si(100). Journal of Applied Physics, 1995, 77, 2329-2338.	1.1	12
129	Nanometerâ€structure writing on Si(100) surfaces using a nonâ€contactâ€mode atomic force microscope. Applied Physics Letters, 1994, 65, 1415-1417.	1.5	37
130	Transferâ€matrix analysis of waveguide phase modulator using the linear electroâ€optic effect of asymmetric quantum wells. Journal of Applied Physics, 1994, 76, 4903-4905.	1.1	1
131	Boron delta doping in Si and SiGe and its application toward field-effect transistor devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 1203.	1.6	11
132	Nanometer scale patterning of silicon (100) surfaces by an atomic force microscope operating in air. Applied Physics Letters, 1994, 64, 2133-2135.	1.5	73
133	Observation of a large capacitive current in a double barrier resonant tunneling diode at resonance. Applied Physics Letters, 1994, 64, 2276-2278.	1.5	13
134	Interface properties of thin oxides grown on strained Ge _x Si _{1-x} layer. Journal of Applied Physics, 1994, 76, 982-986.	1.1	21
135	Strain relief of metastable GeSi layers on Si(100). Journal of Applied Physics, 1994, 75, 4475-4481.	1.1	27
136	Damage and strain in pseudomorphic vs relaxed Ge _x Si _{1-x} layers on Si(100) generated by Si ion irradiation. Journal of Electronic Materials, 1994, 23, 369-373.	1.0	11
137	Epitaxial Ge layers on Si via Ge _x Si _{1-x} O ₂ reduction: The roles of the hydrogen partial pressure and the Ge content. Journal of Electronic Materials, 1994, 23, 437-440.	1.0	6
138	Electron intersubband absorption in Ge/Si _{1-x} Ge _x quantumâ€well structures grown on Si (001) substrate. Applied Physics Letters, 1994, 64, 1256-1258.	1.5	15
139	Dominant photogenerated valley current in a doubleâ€barrier resonantâ€tunneling diode. Applied Physics Letters, 1994, 65, 2999-3001.	1.5	4
140	Steady-State Versus Rapid Thermal Annealing of Phosphorusimplanted Pseudomorphic Si(100)/Ge _{<sub>0.12</sub>Si<sub>0.88</sub>. Materials Research Society Symposia Proceedings, 1994, 342, 51.}	0.1	2
141	Variations of Interfacial Roughness with Epilayer Thickness and Scaling Behavior in Si _{1-x} Ge _x Grown on Si(100) Substrates. Materials Research Society Symposia Proceedings, 1994, 367, 311.	0.1	0
142	Highâ€mobilityâ€channel metalâ€oxideâ€semiconductor fieldâ€effect transistor on strained Si. Applied Physics Letters, 1993, 62, 2853-2855.	1.5	158
143	Carrier transport in GaAs/AlGaAs heterostructures by microwave timeâ€ofâ€flight technique. Applied Physics Letters, 1993, 63, 3491-3493.	1.5	2
144	Intersubband transitions in ap-type δ -doped SiGe/Si quantum well. Physical Review B, 1993, 47, 15638-15647.	1.1	39

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145	Effect of hydrogenation on the luminescence of strained Si _{1-x} Ge _x alloy layers grown by molecular beam epitaxy. Journal of Applied Physics, 1993, 74, 1279-1282.	1.1	9
146	Electron mobility enhancement from coupled wells in delta-doped GaAs. Applied Physics Letters, 1993, 62, 504-506.	1.5	64
147	Bound-to-bound intersubband transitions in a delta-doped p-type Si/SixGe _{1-x} /Si quantum well. Applied Physics Letters, 1993, 62, 1119-1121.	1.5	7
148	Boron delta-doped Si metal semiconductor field-effect transistor grown by molecular beam epitaxy. Applied Physics Letters, 1993, 63, 1363-1365.	1.5	16
149	Ballistic electron emission microscopy of (100)CoGa/n-type GaAs interfaces grown by molecular beam epitaxy. Applied Physics Letters, 1993, 63, 1062-1064.	1.5	3
150	Damage and strain in epitaxial GexSi _{1-x} films irradiated with Si. Journal of Applied Physics, 1993, 74, 6039-6045.	1.1	54
151	Nanocrystalline Ge in SiO ₂ by annealing of GexSi _{1-x} O ₂ in hydrogen. Applied Physics Letters, 1993, 62, 3321-3323.	1.5	34
152	Observation of magnetic-field-induced delocalization: Transition from Anderson insulator to quantum Hall conductor. Physical Review Letters, 1993, 71, 1439-1442.	2.9	158
153	Enhancement of Si hole mobility in coupled delta-doped wells. Applied Physics Letters, 1993, 62, 3455-3457.	1.5	19
154	Microscopic structure of interfaces in Si _{1-x} Ge _x /Si heterostructures and superlattices studied by x-ray scattering and fluorescence yield. Physical Review B, 1993, 47, 16373-16381.	1.1	92
155	Band structure and symmetry analysis of coherently grown Si _{1-x} Ge _x alloys on oriented substrates. Physical Review B, 1993, 47, 1936-1953.	1.1	53
156	Characterization of SixGe _{1-x} /Si heterostructures for device applications using spectroscopic ellipsometry. Journal of Applied Physics, 1993, 74, 586-595.	1.1	11
157	Photoluminescence and optically detected magnetic resonance of Si/Si _{1-x} Ge _x strained-layer superlattices grown by molecular-beam epitaxy. Physical Review B, 1993, 47, 1305-1315.	1.1	25
158	Dopant Activation And Epitaxial Regrowth in P-Implanted Pseudomorphic Ge _{0.12} Si _{0.88} Layers on Si (100). Materials Research Society Symposia Proceedings, 1993, 321, 485.	0.1	6
159	Interband resonant tunneling in InAs/AlSb/GaSb symmetric polytype structures. Physical Review B, 1992, 46, 16012-16017.	1.1	39
160	Oscillator strength for intersubband transitions in strained n-type SixGe _{1-x} quantum wells. Physical Review B, 1992, 46, 7682-7690.	1.1	16
161	Intervalence subband transition in SiGe/Si multiple quantum wells normal incident detection. Applied Physics Letters, 1992, 61, 681-683.	1.5	69
162	Luminescence of strained Si _{1-x} Ge _x alloy layers grown by molecular beam epitaxy. Applied Physics Letters, 1992, 61, 2586-2588.	1.5	16

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163	Intersubband absorption in Sb δ -doped molecular beam epitaxy Si quantum well structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 992.	1.6	7
164	Structural characterization of SimGenstrained layer superlattices. Journal of Applied Physics, 1992, 71, 4305-4313.	1.1	8
165	Growth of δ -SiC film on Si substrate by surface reaction using hydrocarbon gas and Si molecular beams in ultrahigh vacuum. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 930.	1.6	17
166	Importance of sample preheating in oxidation of $\text{Ge}_x\text{Si}_{1-x}$. Journal of Applied Physics, 1992, 71, 3626-3627.	1.1	4
167	Instability of a $\text{Ge}_x\text{Si}_{1-x}\text{O}_2$ film on a $\text{Ge}_x\text{Si}_{1-x}$ layer. Journal of Applied Physics, 1992, 72, 4444-4446.	1.1	18
168	Temperature dependences of the E ₀ transitions in bulk Ge and a Ge-rich (Si) _m /(Ge) _n superlattice. Physical Review B, 1992, 45, 1712-1718.	1.1	11
169	Wet oxidation of GeSi at 700 \pm 5 $^\circ$ C. Journal of Applied Physics, 1992, 71, 4015-4018.	1.1	55
170	Interface stoichiometry dependence of the Schottky barrier height of CoGa and GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1923.	1.6	8
171	Theoretical studies of tunneling effect on absorption spectrum of a quantum well with applied electric field. Journal of Applied Physics, 1992, 71, 1383-1387.	1.1	3
172	Variation of the Schottky barrier height of the differently oriented CoGa on GaAs by molecular beam epitaxy. Applied Physics Letters, 1992, 61, 2869-2871.	1.5	3
173	Schottky barrier of epitaxial (100)CoGa on GaAs. Journal of Applied Physics, 1992, 72, 1191-1193.	1.1	3
174	Giant negative magnetoresistance of a degenerate two-dimensional electron gas in the variable-range-hopping regime. Physical Review B, 1992, 46, 12830-12833.	1.1	63
175	Generation of Defects and Strain by Ion Implantation in Ge (100) Single Crystals, and in Pseudomorphic $\text{Ge}_{1-x}\text{Si}_x$ Films Grown on Si (100). Materials Research Society Symposia Proceedings, 1992, 262, 1079.	0.1	7
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